IN THE SPECIFICATION:

Amend the paragraph beginning on p. 7, line 12, as follows:

An initial description will now be made of how a high-frequency ceramic packa according to the embodiment is constructed. FIG. 1 illustrates a ceramic frame plate 12 bra jointed at the reverse side thereof to a jointed metal plate 11 by means of, e.g., a silver/copper s In addition, leads 13 for connection to the outside are brazed to the ceramic frame plate 12 th metallized patterns 14 by means of, e.g., the sliver/copper solder. The metallized patterns formed on the ceramic frame plate 12 on the obverse side thereof. The lead 13 is formed by KV (a Fe-Ni-Co series alloy, called "Kovar" as a brand name) or a 42-alloy (a Ni-Fe alloy). the brazed metal plate 11, ceramic frame plate 12, and leads 13 are nickel-plated and gold-pla metal surfaces thereof, thereby forming the ceramic package 10. The substantially rectan shaped metal plate 11 is provided with fixing cutouts 15 at both ends of the metal plate 1 longitudinal direction thereof for fixing the ceramic package 10. The metal plate 11 is screwed tight on a fixing member (not shown) at the cutouts 15. In the ceramic package 10, semicon electronic components are packaged in a concave cavity 16 on a bottom 16a thereof. The ce frame plate 12 has a hollow portion at the central portion thereof. The cavity 16 is defined be the jointed metal plate 11 and the ceramic frame plate 12. Namely, a semiconductor elec component mounting portion is formed on the bottom 16a of the cavity 16. The pac semiconductor components are then hermetically sealed by means of resin. A metal materi forms the bottom 16a is made from a highly heat-sinking material having a high level of th

thicknesses of said first and second metal plates being substantially equal, said first and second plates being jointed at substantially the same level, and said second metal plate being a substa rectangular plate.